

CMSA50N06N

60V, 12mΩ typ., 50A N-Channel MOSFET

General Description

The CMSA50N06N combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$. This device is ideal for boost converters and synchronous rectifiers for consumer, telecom, industrial power supplies and LED backlighting.

Features

- Low On-Resistance
- 100% Avalanche Tested
- RoHS Compliant

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	60	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^\circ\text{C}$	Continuous Drain Current	50	A
$I_D@T_C=100^\circ\text{C}$	Continuous Drain Current	35	A
I_{DM}	Pulsed Drain Current	150	A
EAS	Single Pulse Avalanche Energy ¹	144	mJ
$P_D@T_C=25^\circ\text{C}$	Total Power Dissipation	70	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient	---	50	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance Junction -Case	---	1.79	$^\circ\text{C/W}$

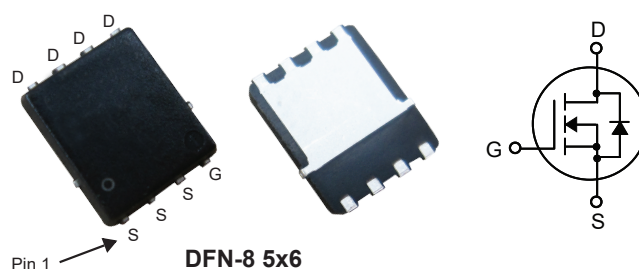
Product Summary

BVDSS	$R_{DS(on)}$ max.	ID
60V	14mΩ	50A

Applications

- Switching application
- Motors, lamps and solenoid control
- LED Lighting and LED Backlight Drivers

DFN-8 5x6 Pin Configuration



Type	Package	Marking
CMSA50N06N	DFN-8 5x6	CMSA50N06N

Electrical Characteristics ($T_J=25^{\circ}\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=250\mu A$	60	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10V$, $I_D=25A$	---	12	14	mΩ
		$V_{GS}=4.5V$, $I_D=20A$	---	13	16	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=250\mu A$	1	---	3	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=60V$, $V_{GS}=0V$, $T_J=25^{\circ}\text{C}$	---	---	1	uA
		$V_{DS}=60V$, $V_{GS}=0V$, $T_J=100^{\circ}\text{C}$	---	---	100	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V$, $V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=5V$, $I_D=25A$	---	36	---	S
R_g	Gate Resistance	$V_{DS}=25V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	2.1	---	Ω
Q_g	Total Gate Charge	$V_{DS}=30V$, $V_{GS}=10V$, $I_D=40A$	---	34	---	nC
Q_{gs}	Gate-Source Charge		---	6	---	
Q_{gd}	Gate-Drain Charge		---	8.5	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=30V$, $V_{GEN}=10V$, $R_G=1\Omega$ $I_D=40A$, $R_L=0.75\Omega$	---	8	---	ns
T_r	Rise Time		---	13	---	
$T_{d(off)}$	Turn-Off Delay Time		---	22	---	
T_f	Fall Time		---	10	---	
C_{iss}	Input Capacitance	$V_{DS}=25V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	2500	---	pF
C_{oss}	Output Capacitance		---	120	---	
C_{rss}	Reverse Transfer Capacitance		---	100	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	$V_G=V_D=0V$, Force Current	---	---	50	A
I_{SM}	Pulsed Source Current		---	---	200	A
V_{SD}	Diode Forward Voltage	$V_{GS}=0V$, $I_S=20A$, $T_J=25^{\circ}\text{C}$	---	0.84	1.25	V

Note :

1.The EAS data shows Max. rating . The test condition is $V_{DD}=30V$, $V_{GS}=10V$, $L=1\text{mH}$, $I_{AS}=17A$.

This product has been designed and qualified for the consumer market.

Cmos assumes no liability for customers' product design or applications.

Cmos reserves the right to improve product design ,functions and reliability without notice.

Typical Characteristics

